Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection

3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	170	mA	
Static characteristics (per transistor)								
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 170 mA; T_j = 25 °C		-	3	4.5	Ω	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	$G1 \longrightarrow G2$
4	S2	source TR2	☐1 ☐2 ☐3	
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX138AKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
NX138AKS	F8%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor		_	'		
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	170	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	110	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	680	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	265	mW
			[1]	-	325	mW
		T _{sp} = 25 °C		-	1.33	W
Per device				'		,
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	nin diode	,	1		-	
I _S	source current	T _{amb} = 25 °C	[1]	-	170	mA

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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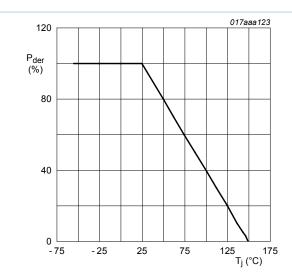


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

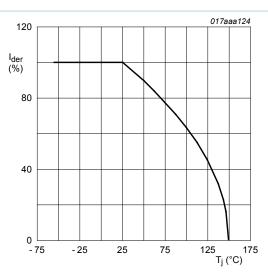
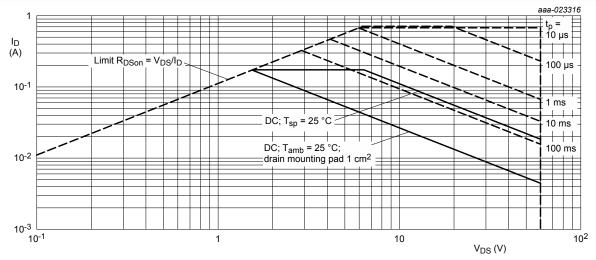


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

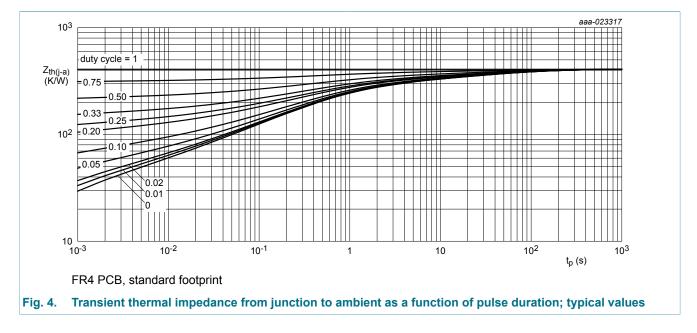
60 V, dual N-channel Trench MOSFET

9. Thermal characteristics

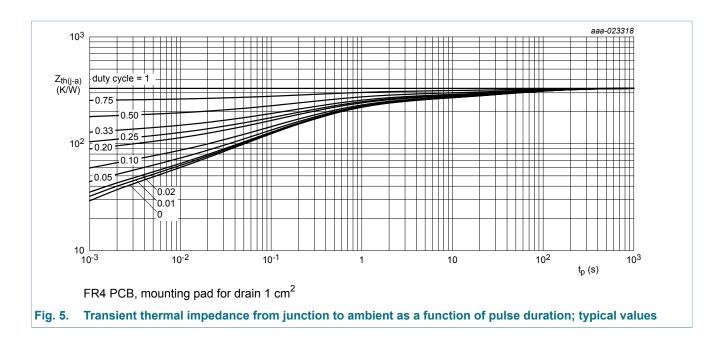
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transist	Per transistor							
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	500	560	K/W	
		[2]	-	450	480	K/W		
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	100	115	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \degree C$	0.8	1.1	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.5	μΑ
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 170 mA; T _j = 25 °C	-	3	4.5	Ω
	resistance	V _{GS} = 10 V; I _D = 170 mA; T _j = 150 °C	-	6	9	Ω
		V_{GS} = 5 V; I_D = 150 mA; T_j = 25 °C	-	3.7	5.2	Ω
		V_{GS} = 4 V; I_D = 130 mA; T_j = 25 °C	-	4	6.3	Ω
		V _{GS} = 2.5 V; I _D = 100 A; T _j = 25 °C	-	5	10	Ω
9fs	forward transconductance	V_{DS} = 10 V; I_{D} = 170 mA; T_{j} = 25 °C	-	3.5	-	S
Dynamic ch	naracteristics (per transist	or)	,			,
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I_{D} = 170 mA; V_{GS} = 10 V;	-	0.9	1.4	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	15	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.3	-	pF
C _{rss}	reverse transfer capacitance		-	1.5	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; I_{D} = 170 mA; V_{GS} = 10 V;	-	8	12	ns
t _r	rise time	$R_{G(ext)} = 75 \Omega; T_j = 25 °C$	-	10	-	ns
t _{d(off)}	turn-off delay time		-	8	20	ns
t _f	fall time		-	5	-	ns
Source-dra	in diode (per transistor)				1	1
V_{SD}	source-drain voltage	I _S = 170 mA; V _{GS} = 0 V; T _j = 25 °C	-	0.8	1.2	V

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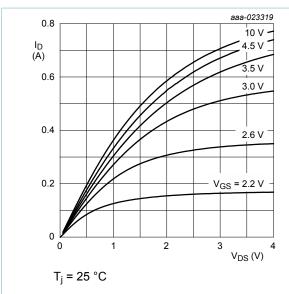


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

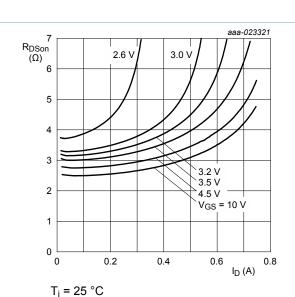


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

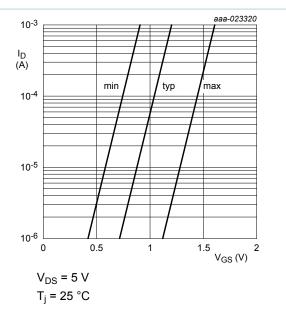


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

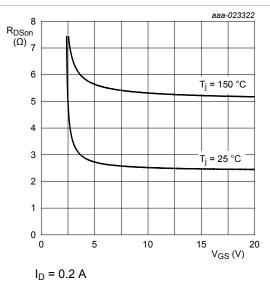


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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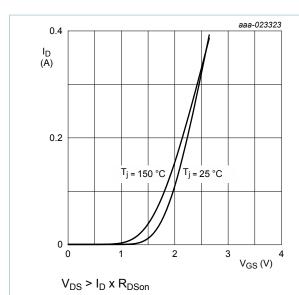


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

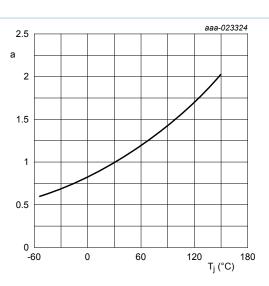


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

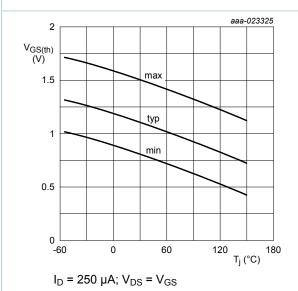


Fig. 12. Gate-source threshold voltage as a function of junction temperature

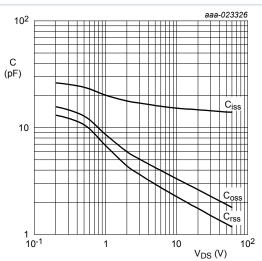


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $f = 1 MHz; V_{GS} = 0 V$

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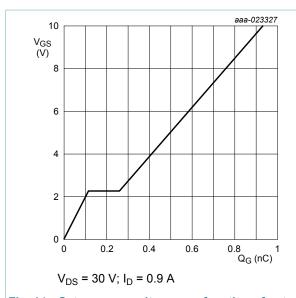


Fig. 14. Gate-source voltage as a function of gate charge; typical values

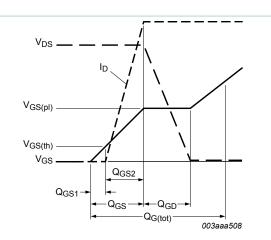


Fig. 15. MOSFET transistor: Gate charge waveform definitions

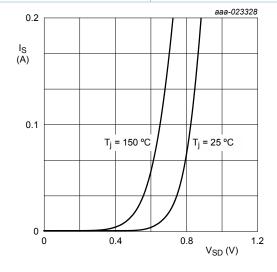
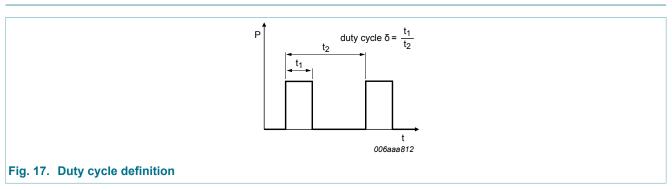


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$

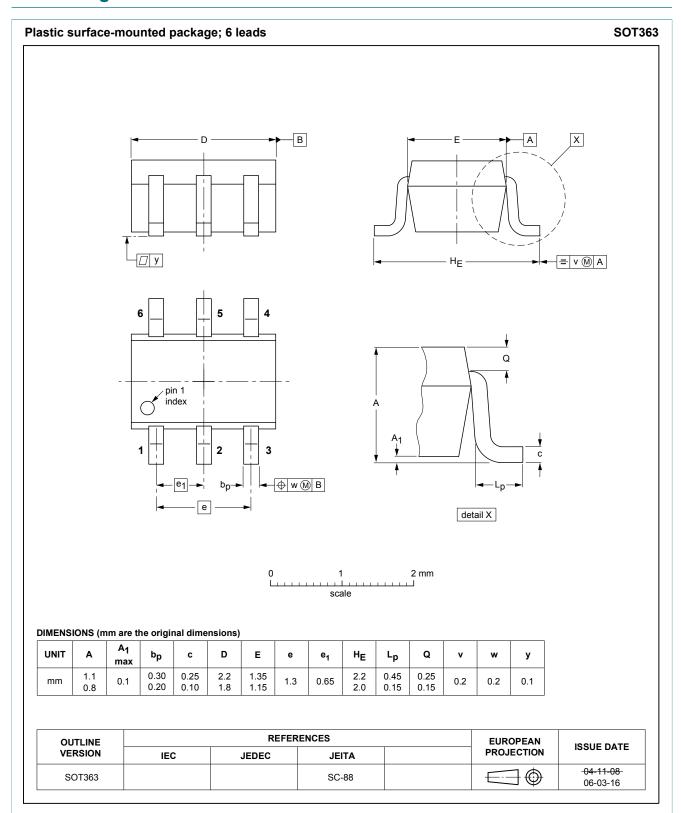


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12. Package outline

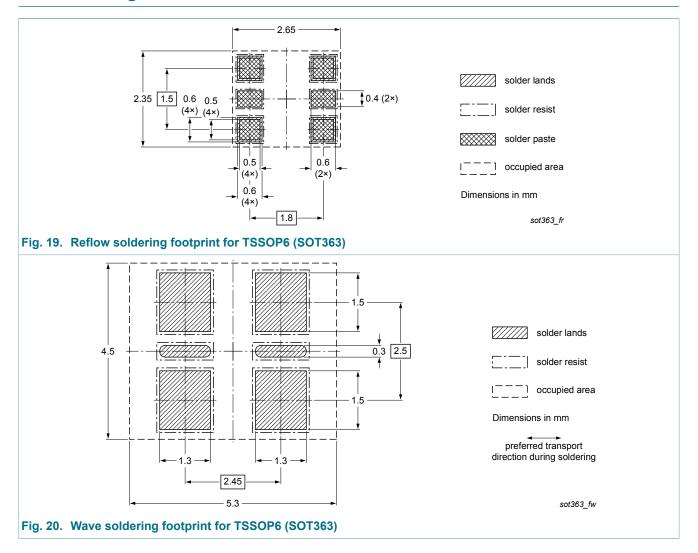


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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX138AKS v.1	20160615	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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